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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/796,109
				Filing Date	March 10, 2004
				First Named Inventor	Joseph F. Brooks
				Art Unit	2812
				Examiner Name	Not Yet Assigned
Sheet	1	of	13	Attorney Docket Number	M4065.1019/P1019

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
AKS	AA	2002/0000666	1/3/2002	Kozicki et al.	
	AB	2002/0072188	6/13/2002	Gilton	
	AC	2002/0106849	08/08/2002	Moore	
	AD	2002/0123169	09/05/2002	Moore et al.	
	AE	2002/0123170	09/05/2002	Moore et al.	
	AF	2002/0123248	09/05/2002	Moore et al.	
	AG	2002/0127886	09/12/2002	Moore et al.	
	AH	2002/0132417	09/09/2002	Li	
	AI	2002/0160551	10/31/2002	Harshfield	
	AJ	2002/0163828	11/07/2002	Krieger et al.	
	AK	2002/0168820	11/2002	Kozicki	
	AL	2002/0168852	11/14/2002	Harshfield et al.	
	AM	2002/0190289	12/19/2002	Harshfield et al.	
	AN	2002/0190350	12/19/2002	Kozicki et al.	
	AO	2003/0001229	01/02/2003	Moore et al.	
	AP	2003/0027416	02/06/2003	Moore	
	AQ	2003/0032254	02/13/2003	Gilton	
	AR	2003/0035314	02/20/2003	Kozicki	
	AS	2003/0035315	02/20/2003	Kozicki	
	AT	2003/0038301	02/27/2003	Moore	
	AU	2003/0043631	03/06/2003	Gilton et al.	
	AV	2003/0045049	03/06/2003	Campbell et al.	
	AW	2003/0045054	03/06/2003	Campbell et al.	
	AX	2003/0047765	03/13/2003	Campbell	
	AY	2003/0047772	03/13/2003	Li	
	AZ	2003/0047773	03/13/2003	Li	
	AA1	2003/0048519	03/13/2003	Kozicki	
	AB1	2003/0049912	03/13/2003	Campbell et al.	
	AC1	2003/0068861	04/10/2003	Li	
	AD1	2003/0068862	04/10/2003	Li	
	AE1	2003/0095426	05/22/2003	Hush et al.	
	AF1	2003/0096497	05/22/2003	Moore et al.	
	AG1	2003/0107105	06/12/2003	Kozicki	
	AH1	2003/0117831	06/26/2003	Hush	
	AI1	2003/0128612	07/10/2003	Moore et al.	
	AJ1	2003/0137869	07/24/2003	Kozicki	
	AK1	2003/0143782	07/31/2003	Gilton et al.	
	AL1	2003/0155589	08/21/2003	Campbell et al.	
	AM1	2003/0155606	08/21/2003	Campbell et al.	
	AN1	2003/0156447	08/21/2003	Kozicki	
	AO1	2003/0156463	08/21/2003	Casper et al.	
	AP1	2003/0209728	11/13/2003	Kozicki et al.	
	AQ1	2003/0209971	11/13/2003	Kozicki et al.	
AKS	AR1	2003/0210564	11/13/2003	Kozicki et al.	

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Sheet	2	of	13	Attorney Docket Number	M4065.1019/P1019

AKS	AS1	US 2003/0212724	11/2003	Ovshinsky et al.	
	AT1	US 2003/0048744	3/2003	Ovshinsky et al.	
	AU1	US 2003/0212725	11/2003	Ovshinsky et al.	
	AV1	US 2004/0035401	2/2004	Ramachandran et al.	
	AW1	3,622,319	11/1971	Sharp	
	AX1	3,743,847	7/1973	Boland	
	AY1	4,269,935	5/1981	Masters et al.	
	AZ1	4,312,938	1/1982	Drexler, et al.	
	AA2	4,316,946	1/1982	Masters, et al.	
	AB2	4,320,191	3/1982	Yoshikawa et al.	
	AC2	4,405,710	9/1983	Balasubramanyam et al.	
	AD2	4,419,421	12/1983	Wichelhaus, et al.	
	AE2	4,499,557	2/1985	Holmberg et al.	
	AF2	4,671,618	06/09/1987	Wu et al.	
	AG2	4,795,657	1/1989	Formigoni et al.	
	AH2	4,800,526	01/24/1989	Lewis	
	AI2	4,804,490	02/14/1989	Pryor et al.	
	AJ2	4,847,674	7/1989	Sliwa et al.	
	AK2	4,920,078	04/24/1990	Bagley et al.	
	AL2	5,177,567	1/1993	Klersy et al.	
	AM2	5,219,788	6/1993	Abermathey et al.	
	AN2	5,238,862	8/1993	Blalock et al.	
	AO2	5,272,359	12/21/1993	Nagasubramanian et al.	
	AP2	5,314,772	5/24/1994	Kozicki	
	AQ2	5,315,131	5/1994	Kishimoto et al.	
	AR2	5,330,630	07/19/1994	Klersy et al.	
	AS2	5,350,484	9/1994	Gardner et al.	
	AT2	5,360,981	11/1994	Owen et al.	
	AU2	5,500,532	3/19/1996	Kozicki et al.	
	AV2	5,512,328	4/1996	Yoshimura et al.	
	AW2	5,512,773	4/1996	Wolf et al.	
	AX2	5,726,083	3/1998	Takaishi	
	AY2	5,751,012	5/12/1998	Wolstenholme et al.	
	AZ2	5,761,115	6/1998	Kozicki et al.	
	AA3	5,789,277	8/1998	Zahorik et al.	
	AB3	5,814,527	9/29/1998	Wolstenholme et al	
	AC3	5,818,749	10/06/1998	Harshfield	
	AD3	5,837,564	11/17/1998	Sandhu et al.	
	AE3	5,841,150	11/1998	Gonzalez et al.	
	AF3	5,846,889	12/1998	Harbison et al.	
	AG3	5,851,882	12/22/1998	Harshfield	
	AH3	5,869,843	2/9/1999	Harshfield	
	AI3	5,896,312	4/20/1999	Kozicki et al.	
	AJ3	5,914,893	6/22/1999	Kozicki et al.	
	AK3	5,920,788	7/1999	Reinberg	
	AL3	5,933,365	08/03/1999	Klersy et al.	
	AM3	5,998,066	12/1999	Block et al.	
	AN3	6,031,287	2/29/2000	Harshfield	
AKS	AO3	6,072,716	06/06/2000	Jacobson et al.	

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AKS	AP3	6,077,729	6/2000	Harshfield	
	AQ3	6,084,796	7/4/2000	Kozicki et al.	
	AR3	6,177,338	1/2001	Liaw et al.	
	AS3	6,117,720	9/2000	Harshfield	
	AT3	6,143,604	11/2000	Chiang et al.	
	AU3	6,236,059	5/2001	Wolsteinholme et al.	
	AV3	6,297,170	10/2001	Gabriel et al.	
	AW3	6,300,684	10/2001	Gonzalez et al.	
	AX3	6,316,784	11/2001	Zahorik et al.	
	AY3	6,329,606	12/2001	Freyman et al.	
	AZ3	6,348,365	2/19/2002	Moore et al.	
	AA4	6,350,679	2/2002	McDaniel et al.	
	AB4	6,376,284	4/2002	Gonzalez et al.	
	AC4	6,388,324	5/14/2002	Kozicki et al.	
	AD4	6,391,688	5/2002	Gonzalez et al.	
	AE4	6,414,376	7/2002	Thakur et al.	
	AF4	6,418,049	7/9/2002	Kozicki et al.	
	AG4	6,420,725	7/16/2002	Harshfield	
	AH4	6,423,628	7/2002	Li et al.	
	AI4	6,440,837	8/27/2002	Harshfield	
	AJ4	6,469,364	10/2002	Kozicki	
	AK4	6,473,332	10/2002	Ignatiev et al.	
	AL4	6,487,106	11/26/2002	Kozicki	
	AM4	RE 37,259E	7/2001	Ovshinsky	
	AN4	3,271,591	9/1966	Ovshinsky	
	AO4	3,961,314	6/1976	Klose et al.	
	AP4	3,966,317	6/1976	Wacks et al.	
	AQ4	3,983,542	11/1976	Ovshinsky	
	AR4	3,988,720	10/1976	Ovshinsky	
	AS4	4,177,474	12/1979	Ovshinsky	
	AT4	4,267,261	5/1981	Hallman et al.	
	AU4	4,597,162	7/1986	Johnson et al.	
	AV4	4,608,296	8/1986	Keem et al.	
	AW4	4,637,895	1/1987	Ovshinsky et al.	
	AX4	4,646,266	2/1987	Ovshinsky et al.	
	AY4	4,664,939	5/1987	Ovshinsky	
	AZ4	4,668,968	5/1987	Ovshinsky et al.	
	AA5	4,670,763	6/1987	Ovshinsky et al.	
	AB5	4,673,957	6/1987	Ovshinsky et al.	
	AC5	4,678,679	7/1987	Ovshinsky	
	AD5	4,696,758	9/1987	Ovshinsky et al.	
	AE5	4,698,234	10/1987	Ovshinsky et al.	
	AF5	4,710,899	12/1987	Young et al.	
	AG5	4,728,406	3/1988	Banerjee et al.	
	AH5	4,737,379	4/1988	Hudgens et al.	
	AI5	4,766,471	8/1988	Ovshinsky et al.	
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	AK5	4,775,425	10/1988	Guha et al.	
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Sheet	4	of	13	Attorney Docket Number	M4065.1019/P1019

AKS	AM5	4,809,044	2/1989	Pryor et al.	
	AN5	4,818,717	4/1989	Johnson et al.	
	AO5	4,843,443	6/1989	Ovshinsky et al.	
	AP5	4,845,533	7/1989	Pryor et al.	
	AQ5	4,853,785	8/1989	Ovshinsky et al.	
	AR5	4,891,330	1/1990	Güha et al.	
	AS5	5,128,099	7/1992	Strand et al.	
	AT5	5,159,661	10/1992	Ovshinsky et al.	
	AU5	5,166,758	11/1992	Ovshinsky et al.	
	AV5	5,177,567	1/1993	Klersy et al.	
	AW5	5,296,716	3/1994	Ovshinsky et al.	
	AX5	5,335,219	8/1994	Ovshinsky et al.	
	AY5	5,359,205	10/1994	Ovshinsky	
	AZ5	5,341,328	8/1994	Ovshinsky et al.	
	AA6	5,406,509	4/1995	Ovshinsky et al.	
	AB6	5,414,271	5/1995	Ovshinsky et al.	
	AC6	5,534,711	7/1996	Ovshinsky et al.	
	AD6	5,534,712	7/1996	Ovshinsky et al.	
	AE6	5,536,947	7/1996	Klersy et al.	
	AF6	5,543,737	8/1996	Ovshinsky	
	AG6	5,591,501	1/1997	Ovshinsky et al.	
	AH6	5,596,522	1/1997	Ovshinsky et al.	
	AI6	5,687,112	11/1997	Ovshinsky	
	AJ6	5,694,054	12/1997	Ovshinsky et al.	
	AK6	5,714,768	2/1998	Ovshinsky et al.	
	AL6	5,825,046	10/1998	Czubatyj et al.	
	AM6	5,912,839	6/1999	Ovshinsky et al.	
	AN6	5,933,365	8/1999	Klersy et al.	
	AO6	6,011,757	1/2000	Ovshinsky	
	AP6	6,087,674	7/2000	Ovshinsky et al.	
	AQ6	6,141,241	10/2000	Ovshinsky et al.	
	AR6	6,339,544	1/2002	Chiang et al.	
	AS6	6,404,665	6/2002	Lowery et al.	
	AT6	6,429,064	8/2002	Wicker	
	AU6	6,437,383	8/2002	Xu	
	AV6	6,462,984	10/2002	Xu et al.	
	AW6	6,480,438	11/2002	Park	
	AX6	6,487,113	11/2002	Park et al.	
	AY6	6,501,111	12/2002	Lowery	
	AZ6	6,507,061	1/2003	Hudgens et al.	
	AA7	6,511,862	1/2003	Hudgens et al.	
	AB7	6,511,867	1/2003	Lowery et al.	
	AC7	6,512,241	1/2003	Lai	
	AD7	6,514,805	2/2003	Xu et al.	
	AE7	6,531,373	3/2003	Gill et al.	
	AF7	6,534,781	3/2003	Dennison	
	AG7	6,545,287	4/2003	Chiang	
	AH7	6,545,907	4/2003	Lowery et al.	
AKS	AI7	6,555,860	4/2003	Lowery et al.	

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AKS	AJ7	6,563,164	5/2003	Lowery et al.	
	AK7	6,566,700	5/2003	Xu	
	AL7	6,567,293	5/2003	Lowery et al.	
	AM7	6,569,705	5/2003	Chiang et al.	
	AN7	6,570,784	5/2003	Lowery	
	AO7	6,576,921	6/2003	Lowery	
	AP7	6,586,761	7/2003	Lowery	
	AQ7	6,589,714	7/2003	Maimon et al.	
	AR7	6,590,807	7/2003	Lowery	
	AS7	6,593,176	7/2003	Dennison	
	AT7	6,597,009	7/2003	Wicker	
	AU7	6,605,527	8/2003	Dennison et al.	
	AV7	6,613,604	9/2003	Maimon et al.	
	AW7	6,621,095	9/2003	Chiang et al.	
	AX7	6,625,054	9/2003	Lowery et al.	
	AY7	6,642,102	11/2003	Xu	
	AZ7	6,646,297	11/2003	Dennison	
	AA8	6,649,928	11/2003	Dennison	
	AB8	6,667,900	12/2003	Lowery et al.	
	AC8	6,671,710	12/2003	Ovshinsky et al.	
	AD8	6,673,700	1/2004	Dennison et al.	
	AE8	6,674,115	1/2004	Hudgens et al.	
	AF8	6,687,427	2/2004	Ramalingam et al.	
	AG8	6,690,026	2/2004	Peterson	
	AH8	6,696,355	2/2004	Dennison	
	AI8	6,687,153	2/2004	Lowery	
	AJ8	6,707,712	3/2004	Lowery	
AKS	AK8	6,714,954	3/2004	Ovshinsky et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ^o
		Country Code ² -Number ³ -Kind Code ⁴ (if known)					
AKS J	BA	56126916		10/19981	Akira et al.		
	BB	WO 97/48032		12/18/1997	Kozicki et al.		
	BC	WO 99/28914		06/10/1999	Kozicki et al.		
	BD	WO 00/48196		08/17/2000	Kozicki et al.		
AKS	BE	WO 02/21542		03/14/2002	Kozicki et al.		

Examiner Signature	<i>Asok Kumar Sarhan</i>	Date Considered	11/29/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
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AKS	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.		
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.		
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.		
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.		
	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.		
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.		
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810		
	CL	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp. 1-6 (Pre-May 2000).		
	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
	CN	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.		
	CO	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag ₇ GeSe ₅ I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.		
	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.		
	CQ	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag ₂ Se-M, Thin solid films 70 (1980) L1-L4.		
	CR	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.		
	CS	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.		
	CT	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.		
AKS	CU	Bernede, J.C.; Conan, A.; Fousenan't, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag ₂ Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.		

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AKS	CV	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al ₂ O ₃ -Ag ₂ -xSe _{1+x} thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	
	CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg ₄ I ₅ , Solid State Ionics 70/71 (1994) 72-76.	
	CX	Boolchand, P., The maximum in glass transition temperature (T _g) near x=1/3 in GexSe _{1-x} Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CY	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
	CZ	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/796,109
				Filing Date	March 10, 2004
				First Named Inventor	Joseph F. Brooks
				Group Art Unit	2812
				Examiner Name	Not Yet Assigned
Sheet	13	of	13	Attorney Docket Number	M4065.1019/P1019

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Examiner Signature	Asst. Examiner Sachar	Date Considered	11/29/05
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